

EVLYS LTD. - POWER SEMICONDUCTORS DEVICES - Wholesale and Retail.

Fast Thyristor Type **FDT80-1600-28**

Low switching losses / Low reverse recovery charge
Distributed amplified gate for high di_T/dt

Mean on-state current	I_{TAV}		1600 A		
Repetitive peak off-state voltage	V_{DRM}		2000...2800 V		
Repetitive peak reverse voltage	V_{RRM}				
Turn-off time	t_q		50.0, 63.0 μs		
V_{DRM}, V_{RRM}, V	2000	2200	2400	2600	2800
Voltage code	20	22	24	26	28
$T_j, ^\circ C$	-60...+125				

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Mean on-state current	A	1600 2060 3029	$T_c=96^\circ C$; Double side cooled; $T_c=85^\circ C$; Double side cooled; $T_c=55^\circ C$; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	2512	$T_c=96^\circ C$; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	40.0 46.0	$T_j=T_{jmax}$ $T_j=25^\circ C$	180° half-sine wave; $t_p=10$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=I_{FGM}$; $V_G=20$ V; $t_{GP}=50$ μs ; $di_G/dt=2$ A/ μs
			42.0 48.0	$T_j=T_{jmax}$ $T_j=25^\circ C$	180° half-sine wave; $t_p=8.3$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=I_{FGM}$; $V_G=20$ V; $t_{GP}=50$ μs ; $di_G/dt=2$ A/ μs
I^2t	Safety factor	$A^2s \cdot 10^3$	8000 10500	$T_j=T_{jmax}$ $T_j=25^\circ C$	180° half-sine wave; $t_p=10$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=I_{FGM}$; $V_G=20$ V; $t_{GP}=50$ μs ; $di_G/dt=2$ A/ μs
			7300 9500	$T_j=T_{jmax}$ $T_j=25^\circ C$	180° half-sine wave; $t_p=8.3$ ms; single pulse; $V_D=V_R=0$ V; Gate pulse: $I_G=I_{FGM}$; $V_G=20$ V; $t_{GP}=50$ μs ; $di_G/dt=2$ A/ μs
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	2000...2800	$T_{jmin} < T_j < T_{jmax}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	2100...2900	$T_{jmin} < T_j < T_{jmax}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6 \cdot V_{DRM}$ $0.6 \cdot V_{RRM}$	$T_j=T_{jmax}$; Gate open	

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TRIGGERING				
I_{FGM}	Peak forward gate current	A	10	$T_j = T_{j\max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	8	$T_j = T_{j\max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ μ s	2500	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 5800$ A; Gate pulse: $I_G = 2$ A; $V_G = 20$ V; $t_{GP} = 50$ μ s; $di_G/dt = 2$ A/ μ s
THERMAL				
T_{stg}	Storage temperature	$^{\circ}$ C	-60...+50	
T_j	Operating junction temperature	$^{\circ}$ C	-60...+125	
MECHANICAL				
F	Mounting force	kN	40.0...50.0	
a	Acceleration	m/s ²	50	Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.26	$T_j = 25$ $^{\circ}$ C; $I_{TM} = 5024$ A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.360	$T_j = T_{j\max}$;	
r_T	On-state slope resistance, max	m Ω	0.183	$0.5 \pi I_{TAV} < I_T < 1.5 \pi I_{TAV}$	
I_H	Holding current, max	mA	1000	$T_j = 25$ $^{\circ}$ C; $V_D = 12$ V; Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	300	$T_j = T_{j\max}$; $V_D = V_{DRM}$; $V_R = V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage ¹⁾ , min	V/ μ s	200, 320, 500, 1000, 1600, 2000, 2500	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	3.00 3.00 1.50	$T_j = T_{j\min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\max}$	$V_D = 12$ V; $I_D = 3$ A; Direct gate current
I_{GT}	Gate trigger direct current, max	mA	500 300 150	$T_j = T_{j\min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\max}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.35	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$;	
I_{GD}	Gate non-trigger direct current, min	mA	70.00	Direct gate current	
SWITCHING					
t_{gd}	Delay time, max	μ s	1.05	$T_j = 25$ $^{\circ}$ C; $V_D = 1500$ V; $I_{TM} = I_{TAV}$; $di/dt = 200$ A/ μ s;	
t_{gt}	Turn-on time ²⁾ , max	μ s	2.50, 3.20, 4.00, 6.30	Gate pulse: $I_G = 2$ A; $V_G = 20$ V; $t_{GP} = 50$ μ s; $di_G/dt = 2$ A/ μ s	
t_q	Turn-off time ³⁾ , max	μ s	50.0, 63.0	$dv_D/dt = 50$ V/ μ s;	
			63.0, 80.0	$dv_D/dt = 200$ V/ μ s;	
Q_{rr}	Total recovered charge, max	μ C	1250	$T_j = T_{j\max}$; $I_{TM} = 2000$ A;	
t_{rr}	Reverse recovery time, max	μ s	9.0	$di_R/dt = -50$ A/ μ s;	
I_{rrM}	Peak reverse recovery current, max	A	280	$V_R = 100$ V	

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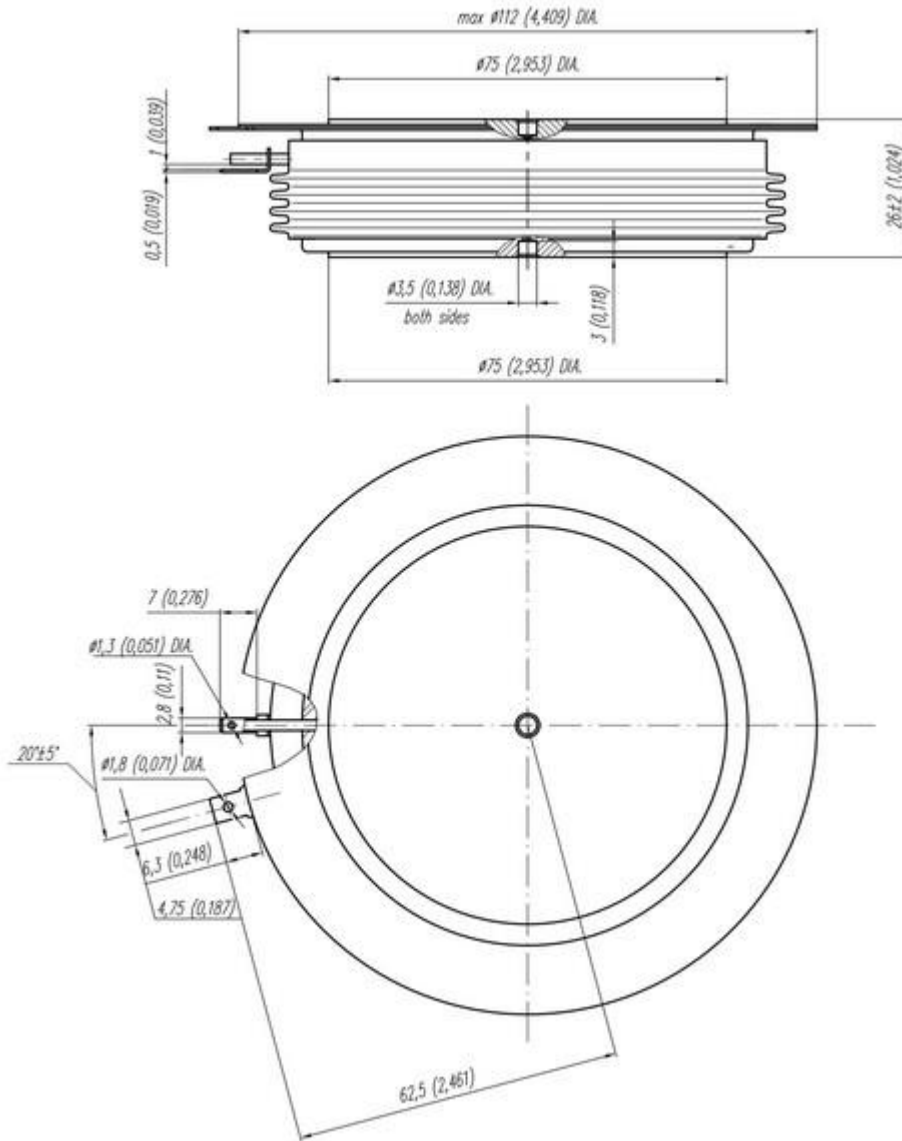
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0085	Direct current	Double side cooled
R_{thjc-A}			0.0187		Anode side cooled
R_{thjc-K}			0.0153		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0020	Direct current	
MECHANICAL					
w	Weight, max	g	1170		
D_s	Surface creepage distance	mm (inch)	36.60 (1.441)		
D_a	Air strike distance	mm (inch)	16.20 (0.638)		

PART NUMBERING GUIDE								NOTES									
FDT	80	1600	28	7	2	3											
1	2	3	4	5	6	7		1) Critical rate of rise of off-state voltage									
1. FDT — Fast Inverter Disc Thyristor								Symbol of Group	4	5	6	7	8	8,5	9		
2. Design version								$(dv_D/dt)_{crit}$, V/ μ s	200	320	500	1000	1600	2000	2500		
3. Mean on-state current, A								2) Turn-on time									
4. Voltage code								Symbol of group	4	3	2						
5. Critical rate of rise of off-state voltage								t_{gt} , μ s	2.50	3.20	4.00					6.30	
6. Group of turn-off time ($dv_D/dt=50$ V/ μ s)								3) Turn-off time ($dv_D/dt=50$ V/ μ s)									
7. Group of turn-on time								Symbol of group	2				1				
								t_q , μ s	50.0				63.0				

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OVERALL DIMENSIONS

Package type: **T.F2**



All dimensions in millimeters (inches)